

## Mastered Techniques

### 1. Characterization of Semiconductor Materials and Nanostructures:

- **Optical:** NSOM<sup>1</sup>, micro-Raman Scattering Spectroscopy, Spectral Ellipsometry, Specular and Diffuse Reflectances, FTIR<sup>2</sup>
- **Nanoscale material mechanical properties:** Nanoindentation, load controlled nano-scratch, surface stiffness by AFM,
- **micro and nano-Topography:** AFM, NSOM
- **Structural:** Synchrotron x-ray nanoProbe, TEM and HRTEM<sup>3</sup>, XRT<sup>4</sup>, anisotropic etching/Nomarski microscopy, OPP<sup>5</sup>, and nano-topography by AFM.
- **Chemical:** STEM Z-Contrast, EELS<sup>6</sup>, micro-FTIR<sup>7</sup> Synchrotron Source, SIMS<sup>8</sup> et  $\mu$ -SIMS imaging,
- **Optoelectronic:** CL,<sup>9</sup> EBIC<sup>10</sup>/SEM, MOS-EBIC, Spectrale Response, LBIC<sup>11</sup>/CSLM<sup>12</sup>.
- **Electrical properties:** I-V<sup>13</sup>, CV<sup>14</sup>, Recombination Lifetime by  $\mu$ PCD<sup>15</sup>, Generation Lifetime by Zerbst Analysis, High Resolution Spreading Resistance,
- **Energy Level Spectroscopy:** electrically active impurities: by DLTS,<sup>16</sup> PICTS,<sup>17</sup>  $\mu$ PCD Injection Level Spectroscopy.

### 2. Sample preparation:

- Sample preparation for TEM.
- Chemical Etchings (Secco, Sirtl, Wright, Schimmel) for defect delineation in semiconductors,
- Surface electrical passivation for charge carrier lifetime measurement,

### 3. Device fabrication techniques and sample preparation:

- Ion Implantation, Neutron Irradiation, Sputtering,
- Epitaxy of silicon
- CVD<sup>18</sup> of silicon dioxide and silicon nitride,
- Oxidation and diffusion of dopants in open tubes furnaces,
- Diffusion of dopants and Antireflective coating in belt furnaces,
- Silicon passivation and impurity gettering,
- Anisotropic dry etching (RIE),
- Evaporation, Photolithography,...

### 4. Photovoltaic Cell Fabrication:

- Solar cell fabrication on crystalline (mono and poly) silicon, and II-VI semiconductors
- P-N junction based devices + back surface field (BSF) or back surface reflector (BSR)
- Thin films solar cells fabrication by electro-deposition and by airless spray,
- Chemical and Electrochemical etching for optical propriety control: textured et porous structures,
- Screen printing, Spin-On, Airless-Spray, Electrodeposition of thin film.

<sup>1</sup> **NSOM:** Near Field Optical Microscopy: (beyond diffraction limits, spatial resolution 50 nanometre)

<sup>2</sup> **FTIR:**Fourier Transform Infra Red

<sup>3</sup> **HRTEM:** High Resolution Transmission Electron Microscopy

<sup>4</sup> **XRT:** x-ray topography using Lang camera. Allows defect imaging in transmission and reflection modes as well as cross-section and limited projection topography (LP-XRT)

<sup>5</sup> **OPP:** Optical Precipitate Profiling: i. e. , Infra Red Scanning Differential Interference Contrast Microscope

<sup>6</sup> **EELS:** Electron Energy Loss Spectroscopy

<sup>7</sup> **micro-FTIR:** Fourier Transform Infra Red couplée a une source Synchrotron (*near*- and *far*-IR)

<sup>8</sup> **SIMS:** Secondary Ion Mass Spectroscopy

<sup>9</sup> **CL:** Cathodoluminescence

<sup>10</sup> **EBIC:** Electron Beam Induced Current: Imaging of carrier recombination current induced in semiconducteurs by electron beam scanning in SEM.

<sup>11</sup> **LBIC:** Light Beam Induced Current, similar to EBIC, but employs a well focused laser beam.

<sup>12</sup> **CSLM:** Confocal Scanning Laser Microscopy

<sup>13</sup> **I-V:** Current Voltage characteristic of devices

<sup>14</sup> **C-V:** Capacitance Voltage characteristic

<sup>15</sup>  **$\mu$ -PCD:** Laser Microwave Photo-Conductance Decay (micro-PCD).

<sup>16</sup> **DLTS:** Deep Level Transient Spectroscopy

<sup>17</sup> **PICTS:** Photo Induced Current Transient Spectroscopy

<sup>18</sup> **CVD:** Chemical Vapor Deposition

5. Computing and Software(s):

- High Performance Computing for materials modeling:
  - Atomistic (quantum mechanics and molecular dynamics): CERIOUS2, UNICHEM, MATERIALS STUDIO,<sup>19</sup> VASP,<sup>20</sup> EDIP,<sup>21</sup> ADESH<sup>22</sup>
  - Simulation d'implantation ionique: SRIM<sup>23</sup>
- Numerical Analysis: Optimization, Simulated Annealing, Newton-Raphson, Non Linear Problems, Linear Algebra, Sparse Matrix, LU factorization, Gauss-Seidel, Finite differences, Implicit and Explicit methods for Resolution of Differential Equations.
- Phenomenological Analysis of thermal, structural, and optical coupled fields by Finite Elements as well as Diffusion and Impurity and Atom and Point Defect Clustering
- Used Finite Element Analysis Software: ANSYS and FEMLAB
- Used Numerical Analysis Packages: Origin/NAG, Numerical Recipes, ISML, LINPACK
- Data Analysis, Statistical Analysis and Experiment Design: ANNOVA, DAAD

6. General Utilities Software(s)

- Numerical and Symbolic Math Tools: MATLAB, MATHCAD, MAPLE.
- Image Processing: Adobe Photoshop, IP image digital processing package, Scion Image<sup>24</sup> (formerly NIH Image), Image Tools, Gimp (under Linux).
- Graphics: AVS, Origin, Gnuplot.

7. Other Software(s)

- Compilers: FORTRAN, Basic, Visual Basic, Pascal, and Assembling language
- Parallel computing: Parallel Fortran and MPI<sup>25</sup>
- Systems: MSDOS, MS Windows, Linux
- Networks: TelNet, FTP, SSH,...
- Macro Languages for automation of Word Processing and Spreadsheets (MS Office)

8. Computer Hardware/Automation:

- LabView software, Test Point software
- Instrument and device interfacing via RS170A, RS232C, IEEE488.
- Transputers INMOS800, INMOS400,
- Micro-controller: Intel 8052.

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<sup>19</sup> CERIOUS2, UNICHEM, MATERIALS STUDIO developed by Accelrys Inc., San Diego

<sup>20</sup> VASP: Vienna Ab-initio Package Simulation

<sup>21</sup> EDIP: Environment Dependent Interaction Potential

<sup>22</sup> ADESH: "Atomistic DEfect Simulation Handler", Casa Engineering, Hopewell Junction, New York, NY.

<sup>23</sup> SRIM: Stopping and Range of Ions in Matter

<sup>24</sup> Scion Image: developpé par NIH

<sup>25</sup> MPI: Message Passing Interface